

CY7C130/CY7C131 CY7C140/CY7C141

Features

- · True Dual-Ported memory cells which allow simultaneous reads of the same memory location
- 1K x 8 organization
- · 0.65-micron CMOS for optimum speed/power
- High-speed access: 15 ns
- Low operating power: I_{CC} = 90 mA (max.)
- · Fully asynchronous operation
- Automatic power-down
- Master CY7C130/CY7C131 easily expands data bus width to 16 or more bits using slave CY7C140/CY7C141
- BUSY output flag on CY7C130/CY7C131; BUSY input on CY7C140/CY7C141
- INT flag for port-to-port communication
- Available in 48-pin DIP (CY7C130/140), 52-pin PLCC and 52-pin TQFP
- · Pin-compatible and functionally equivalent to IDT7130/IDT7140

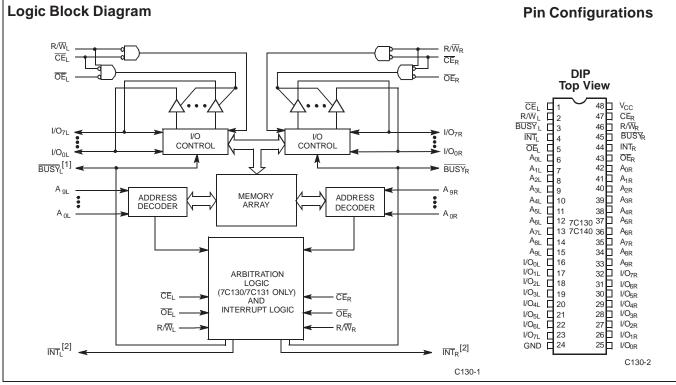
1K x 8 Dual-Port Static Ram

Functional Description

The CY7C130/CY7C131/CY7C140 and CY7C141 are high-speed CMOS 1K by 8 dual-port static RAMs. Two ports are provided permitting independent access to any location in memory. The CY7C130/ CY7C131 can be utilized as either a standalone 8-bit dual-port static RAM or as a master dual-port RAM in conjunction with the CY7C140/CY7C141 slave dual-port device in systems requiring 16-bit or greater word widths. It is the solution to applications requiring shared or buffered data, such as cache memory for DSP, bit-slice, or multiprocessor designs.

Each port has independent control pins; chip enable (\overline{CE}) , write enable (R/W), and output enable (\overline{OE}) . Two flags are provided on each port, BUSY and INT, BUSY signals that the port is trying to access the same location currently being accessed by the other port. INT is an interrupt flag indicating that data has been placed in a unique location (3FF for the left port and 3FE for the right port). An automatic power-down feature is controlled independently on each port by the chip enable (CE) pins.

The CY7C130 and CY7C140 are available in 48-pin DIP. The CY7C131 and CY7C141 are available in 52-pin PLCC and PQFP.



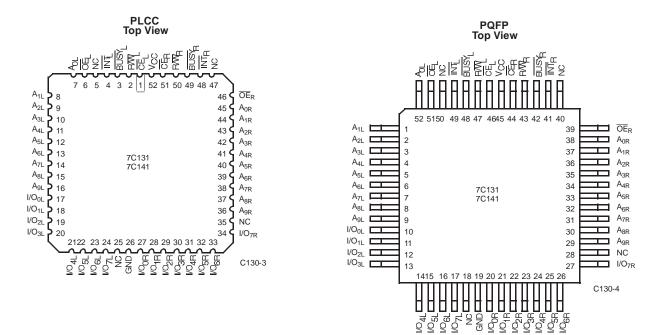
Notes:

1. CY7C130/CY7C131 (Master): <u>BUSY</u> is open drain output and requires pull-up resistor CY7C140/CY7C141 (Slave): BUSY is input.

Open drain outputs: pull-up resistor required



Pin Configuration (continued)



Selection Guide

		7C131-15 ^[3,4] 7C141-15	7C131-25 ^[3] 7C141-25	7C130-30 7C131-30 7C140-30 7C141-30	7C130-35 7C131-35 7C140-35 7C141-35	7C130-45 7C131-45 7C140-45 7C141-45	7C130-55 7C131-55 7C140-55 7C141-55
Maximum Access Time (ns)		15	25	30	35	45	55
Maximum Operating	Com'l/Ind	190	170	170	120	90	90
Current (mA)	Military				170	120	120
Maximum Standby	Com'l/Ind	75	65	65	45	35	35
Current (mA)	Military				65	45	45

Maximum Ratings

(Above which the useful life may be impaired. For user guide-lines, not tested.)
Storage Temperature65°C to +150°C
Ambient Temperature with Power Applied55°C to +125°C
Supply Voltage to Ground Potential (Pin 48 to Pin 24)0.5V to +7.0V
DC Voltage Applied to Outputs in High Z State0.5V to +7.0V
DC Input Voltage3.5V to +7.0V
Output Current into Outputs (LOW)
15 and 25-ns version available only in PLCC/PQFP packages.

Static Discharge Voltage >2001V (per MIL-STD-883, Method 3015) Latch-Up Current...... >200 mA

Operating Range

Range	Ambient Temperature	V _{CC}
Commercial	0°C to +70°C	5V ± 10%
Industrial	–40°C to +85°C	5V ± 10%
Military ^[5]	–55°C to +125°C	5V ± 10%

Shaded area contains preliminary information. T_A is the "instant on" case temperature 4. 5.

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Electrical Characteristics Over the Operating Range^[6]

					-15 ^[3,4] 41-15	7C131 7C14	0-30 ^[3] -25,30 I0-30 -25,30	7C1 7C1	30-35 31-35 40-35 41-35	7C131 7C140	-45,55 -45,55 -45,55 -45,55	
Parameter	Description	Test Condition	ns	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Unit
V _{OH}	Output HIGH Voltage	$V_{CC} = Min., I_{OH} = -$	4.0 mA	2.4		2.4		2.4		2.4		V
V _{OL}	Output LOW	I _{OL} = 4.0 mA			0.4		0.4		0.4		0.4	V
	Voltage	I _{OL} = 16.0 mA ^[7]			0.5		0.5		0.5		0.5	
V _{IH}	Input HIGH Voltage			2.2		2.2		2.2		2.2		V
V _{IL}	Input LOW Voltage				0.8		0.8		0.8		0.8	V
I _{IX}	Input Leakage Current	$GND \le V_I \le V_{CC}$		-5	+5	-5	+5	-5	+5	-5	+5	μA
I _{OZ}	Output Leakage Current	$GND \le V_O \le V_{CC}$, Output Disabled		-5	+5	-5	+5	-5	+5	-5	+5	μA
I _{OS}	Output Short Circuit Current ^[8, 9]	V _{CC} = Max., V _{OUT} = GND			-350		-350		-350		-350	mA
I _{CC}	V _{CC} Operating	$\overline{CE} = V_{IL},$	Com'l		190		170		120		90	mA
	Supply Current	Outputs Open, f = f _{MAX} ^[10]	Mil						170		120	
I _{SB1}	Standby Current	\overline{CE}_{L} and $\overline{CE}_{R} \ge V_{IH}$, f = f _{MAX} ^[10]	Com'l		75		65		45		35	mA
	Both Ports, TTL Inputs	V_{IH} , $f = f_{MAX}^{[10]}$	Mil						65		45	
I _{SB2}	Standby Current	$\overline{CE}_{L} \text{ or } \overline{CE}_{R} \ge V_{IH},$	Com'l		135		115		90		75	mA
	One Port, TTL Inputs	Active Port Out- puts Open, $f = f_{MAX}^{[10]}$	Mil						115		90	
I _{SB3}	Standby Current	Both Ports CE	Com'l		15		15		15		15	mA
	Both Ports, CMOS Inputs	and $\overline{CE}_R \ge V_{CC} - 0.2V$, $V_{IN} \ge V_{CC} - 0.2V$ or $V_{IN} \le 0.2V$, f = 0	Mil						15		15	-
I _{SB4}	Standby Current	One Port CE _L or	Com'l		125		105		85		70	mA
	One Port, CMOS Inputs	$\label{eq:constraint} \begin{split} \overline{CE}_R &\geq V_{CC} - 0.2V, \\ V_{IN} &\geq V_{CC} - 0.2V \\ \text{or } V_{IN} &\leq 0.2V, \\ \text{Active Port Outputs} \\ \text{Open}, \\ f &= f_{MAX}^{[10]} \end{split}$	Mil						105		85	

Notes:

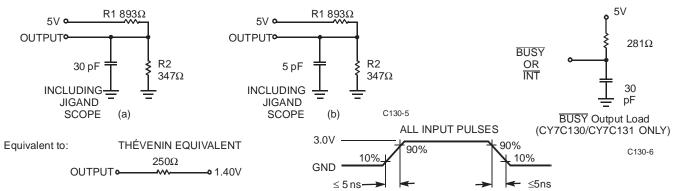
See the last page of this specification for Group A subgroup testing information.
 BUSY and INT pins only.
 Duration of the short circuit should not exceed 30 seconds.
 This parameter is guaranteed but not tested.
 At f=f_{MAX}, address and data inputs are cycling at the maximum frequency of read cycle of 1/t_{RC} and using AC Test Waveforms input levels of GND to 3V.

Capacitance^[9]

Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	$T_A = 25^{\circ}C, f = 1 \text{ MHz},$	15	pF
C _{OUT}	Output Capacitance	$V_{CC} = 5.0V$	10	pF



AC Test Loads and Waveforms



Switching Characteristics Over the Operating Range^[6,11]

		7C131 7C14	-15 ^[3,4] 41-15	7C130-25 ^[3] 7C131-25 7C140-25 7C141-25		7C130-30 7C131-30 7C140-30 7C141-30			
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Unit	
READ CYCL	E	-	-						
t _{RC}	Read Cycle Time	15		25		30		ns	
t _{AA}	Address to Data Valid ^[12]		15		25		30	ns	
t _{OHA}	Data Hold from Address Change	0		0		0		ns	
t _{ACE}	CE LOW to Data Valid ^[12]		15		25		30	ns	
t _{DOE}	OE LOW to Data Valid ^[12]		10		15		20	ns	
t _{LZOE}	OE LOW to Low Z ^[9,13, 14]	3		3		3		ns	
t _{HZOE}	OE HIGH to High Z ^[9,13, 14]		10		15		15	ns	
t _{LZCE}	CE LOW to Low Z ^[9,13, 14]	3		5		5		ns	
t _{HZCE}	CE HIGH to High Z ^[9,13, 14]		10		15		15	ns	
t _{PU}	CE LOW to Power-Up ^[9]	0		0		0		ns	
t _{PD}	CE HIGH to Power-Down ^[9]		15		25		25	ns	
WRITE CYCI	-E ^[15]								
t _{WC}	Write Cycle Time	15		25		30		ns	
t _{SCE}	CE LOW to Write End	12		20		25		ns	
t _{AW}	Address Set-Up to Write End	12		20		25		ns	
t _{HA}	Address Hold from Write End	2		2		2		ns	
t _{SA}	Address Set-Up to Write Start	0		0		0		ns	
t _{PWE}	R/W Pulse Width	12		15		25		ns	
t _{SD}	Data Set-Up to Write End	10		15		15		ns	
t _{HD}	Data Hold from Write End	0		0		0		ns	
t _{HZWE}	R/\overline{W} LOW to High $Z^{[14]}$		10		15		15	ns	
t _{LZWE}	R/\overline{W} HIGH to Low $Z^{[14]}$	0		0		0		ns	

Notes:

11. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading of the specified

12.

13.

14. 15.

At any given temperature and voltage condition for any given device, t_{HZCE} is less than t_{LZCE} and t_{HZCE} is less than t_{LZCE} . At any given temperature and voltage condition for any given device, t_{HZCE} is less than t_{LZCE} is less than t_{LZCE} . At any given temperature and voltage condition for any given device, t_{HZCE} is less than t_{LZCE} is less than t_{LZCE} . At any given temperature and voltage condition for any given device, t_{HZCE} is less than t_{LZCE} is less than t_{LZCE} . At any given temperature and voltage condition for any given device, t_{HZCE} is less than t_{LZCE} is less than t_{LZCE} . t_{LZCE} , t_{LZWE} , t_{HZCE} , t_{HZCE} , t_{HZCE} and t_{HZWE} are tested with C_L = 5pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady state voltage. The internal write time of the memory is defined by the overlap of CS LOW and R/W LOW. Both signals must be low to initiate a write and either signal can terminate a write by going high. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write



Switching Characteristics Over the Operating Range^[6,11] (continued)

		7C131 7C1	-15 ^[3,4] 41-15	7C130-25 ^[3] 7C131-25 7C140-25 7C141-25		7C130-30 7C131-30 7C140-30 7C141-30		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Unit
BUSY/INTER	RRUPT TIMING							
t _{BLA}	BUSY LOW from Address Match		15		20		20	ns
t _{BHA}	BUSY HIGH from Address Mismatch ^[16]		15		20		20	ns
t _{BLC}	BUSY LOW from CE LOW		15		20		20	ns
t _{BHC}	BUSY HIGH from CE HIGH ^[16]		15		20		20	ns
t _{PS}	Port Set Up for Priority	5		5		5		ns
t _{WB} ^[17]	R/W LOW after BUSY LOW	0		0		0		ns
t _{WH}	R/W HIGH after BUSY HIGH	13		20		30		ns
t _{BDD}	BUSY HIGH to Valid Data		15		25		30	ns
t _{DDD}	Write Data Valid to Read Data Valid		Note 18		Note 18		Note 18	ns
t _{WDD}	Write Pulse to Data Delay		Note 18		Note 18		Note 18	ns
INTERRUPT	TIMING							
t _{WINS}	R/W to INTERRUPT Set Time		15		25		25	ns
t _{EINS}	CE to INTERRUPT Set Time		15		25		25	ns
t _{INS}	Address to INTERRUPT Set Time		15		25		25	ns
t _{OINR}	OE to INTERRUPT Reset Time ^[16]		15		25		25	ns
t _{EINR}	CE to INTERRUPT Reset Time ^[16]		15		25		25	ns
t _{INR}	Address to INTERRUPT Reset Time ^[16]		15		25		25	ns

Notes:

Notes:
16. These parameters are measured from the input signal changing, until the output pin goes to a high-impedance state.
7. CY7C140/CY7C141 only.
18. A write operation on Port A, where Port A has priority, leaves the data on Port B's outputs undisturbed until one access time after one of the following: BUSY on Port B goes HIGH. Port B's address is toggled. CE for Port B is toggled during valid read.

Switching Characteristics Over the Operating Range^[6,11]

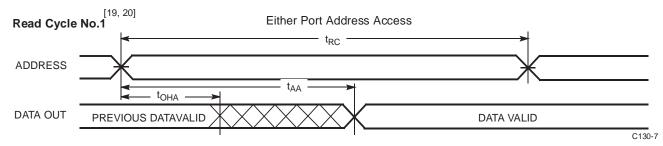
		7C130-35 7C131-35 7C140-35 7C141-35		7C130-45 7C131-45 7C140-45 7C141-45		7C130-55 7C131-55 7C140-55 7C141-55		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCL	E							
t _{RC}	Read Cycle Time	35		45		55		ns
t _{AA}	Address to Data Valid ^[12]		35		45		55	ns
t _{OHA}	Data Hold from Address Change	0		0		0		ns
t _{ACE}	CE LOW to Data Valid ^[12]		35		45		55	ns
t _{DOE}	OE LOW to Data Valid ^[12]		20		25		25	ns
t _{LZOE}	OE LOW to Low Z ^[9,13, 14]	3		3		3		ns
t _{HZOE}	OE HIGH to High Z ^[9,13, 14]		20		20		25	ns
t _{LZCE}	CE LOW to Low Z ^[9,13, 14]	5		5		5		ns
t _{HZCE}	CE HIGH to High Z ^[9,13, 14]		20		20		25	ns
t _{PU}	CE LOW to Power-Up ^[9]	0		0		0		ns
t _{PD}	CE HIGH to Power-Down ^[9]		35		35		35	ns



Switching Characteristics Over the Operating $Range^{[6,11]}$ (continued)

		7C13 7C14	30-35 31-35 40-35 41-35	7C13 7C14	7C130-45 7C131-45 7C140-45 7C141-45		7C130-55 7C131-55 7C140-55 7C141-55	
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CYC	LE ^[15]							
t _{WC}	Write Cycle Time	35		45		55		ns
t _{SCE}	CE LOW to Write End	30		35		40		ns
t _{AW}	Address Set-Up to Write End	30		35		40		ns
t _{HA}	Address Hold from Write End	2		2		2		ns
t _{SA}	Address Set-Up to Write Start	0		0		0		ns
t _{PWE}	R/W Pulse Width	25		30		30		ns
t _{SD}	Data Set-Up to Write End	15		20		20		ns
t _{HD}	Data Hold from Write End	0		0		0		ns
t _{HZWE}	R/\overline{W} LOW to High $Z^{[14]}$		20		20		25	ns
t _{LZWE}	R/W HIGH to Low Z ^[14]	0		0		0		ns
BUSY/INTE	RRUPT TIMING							
t _{BLA}	BUSY LOW from Address Match		20		25		30	ns
t _{BHA}	BUSY HIGH from Address Mismatch ^[16]		20		25		30	ns
t _{BLC}	BUSY LOW from CE LOW		20		25		30	ns
t _{BHC}	BUSY HIGH from CE HIGH ^[16]		20		25		30	ns
t _{PS}	Port Set Up for Priority	5		5		5		ns
t _{WB} [17]	R/W LOW after BUSY LOW	0		0		0		ns
t _{WH}	R/W HIGH after BUSY HIGH	30		35		35		ns
t _{BDD}	BUSY HIGH to Valid Data		35		45		45	ns
t _{DDD}	Write Data Valid to Read Data Valid		Note 18		Note 18		Note 18	ns
t _{WDD}	Write Pulse to Data Delay		Note 18		Note 18		Note 18	ns
INTERRUPT	TIMING							
t _{WINS}	R/W to INTERRUPT Set Time		25		35		45	ns
t _{EINS}	CE to INTERRUPT Set Time		25		35		45	ns
t _{INS}	Address to INTERRUPT Set Time		25		35		45	ns
t _{OINR}	OE to INTERRUPT Reset Time ^[16]		25		35		45	ns
t _{EINR}	CE to INTERRUPT Reset Time ^[16]		25		35		45	ns
t _{INR}	Address to INTERRUPT Reset Time ^[16]		25		35		45	ns

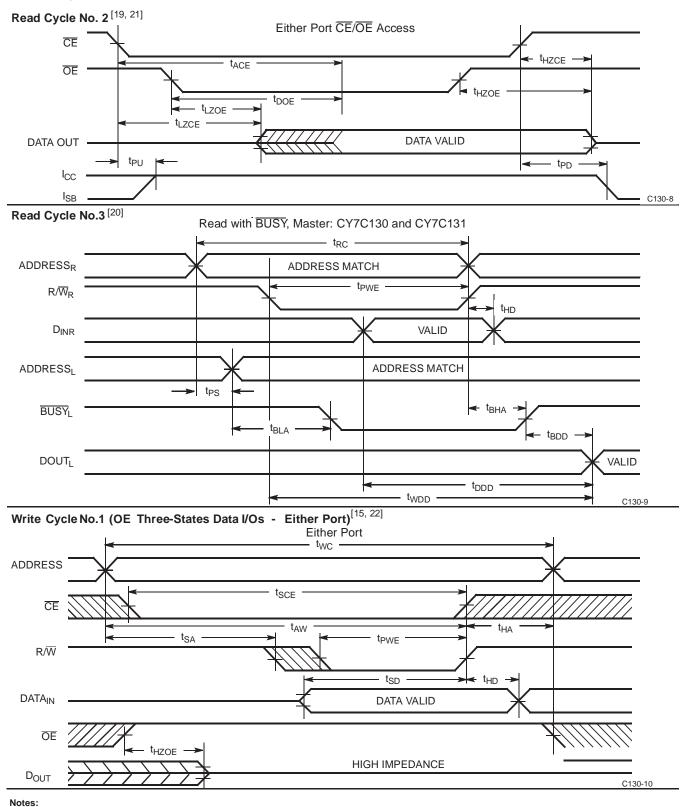
Switching Waveforms



Notes:

^{19.} R/W is HIGH for read cycle. 20. Device is continuously selected, $\overline{CE} = V_{IL}$ and $\overline{OE} = V_{IL}$.



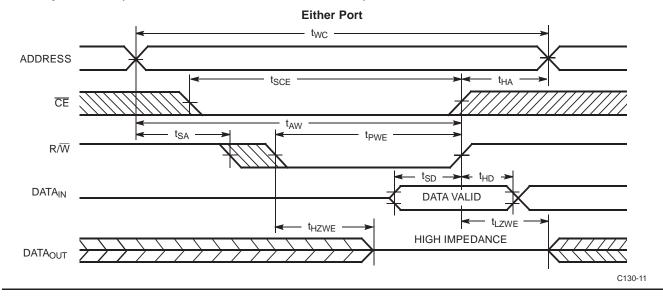


^{21.} 22.

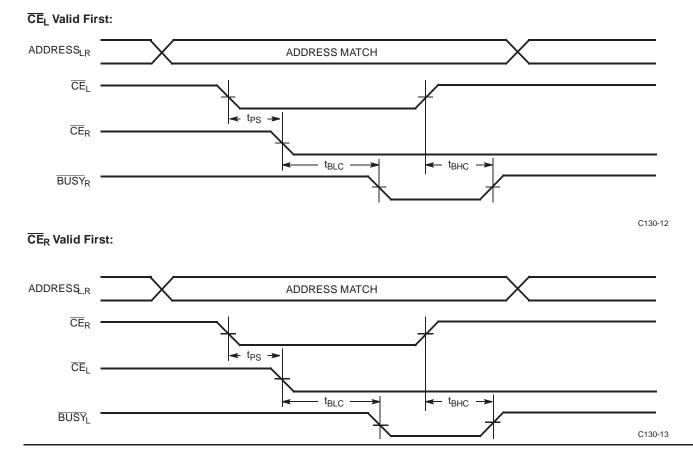
Address valid prior to or coincident with \overline{CE} transition LOW. If \overline{OE} is LOW during a R/W controlled write cycle, the write pulse width must be the larger of t_{PWE} or t_{HZWE} + t_{SD} to allow the data I/O pins to enter high impedance and for data to be placed on the bus for the required t_{SD}.



Write Cycle No. 2 ($R\overline{/W}$ Three-States Data I/Os - Either Port)^[16, 23]



Busy Timing Diagram No. 1 (CE Arbitration)

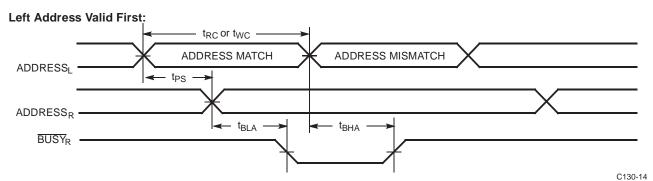


Note:

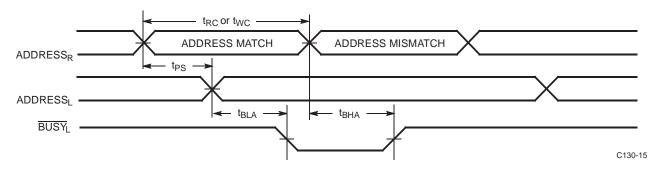
23. If the CE LOW transition occurs simultaneously with or after the R/W LOW transition, the outputs remain in the high-impedance state



Busy Timing Diagram No. 2 (Address Arbitration)

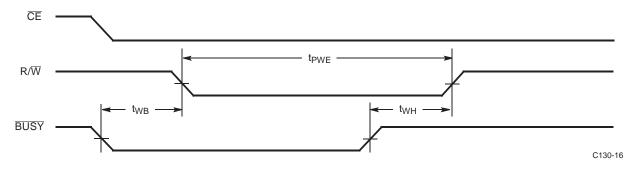


Right Address Valid First:

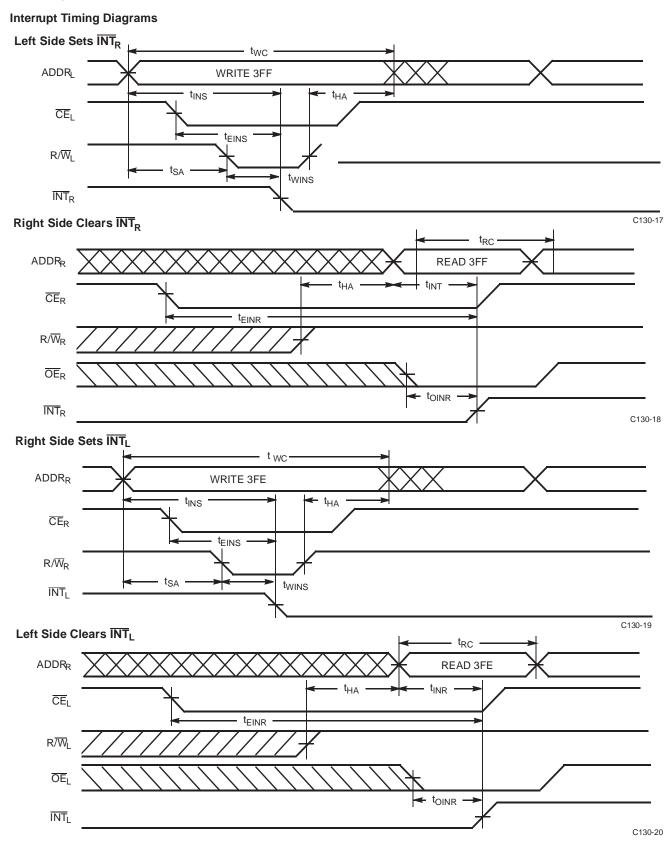


Busy Timing Diagram No. 3

Write with BUSY (Slave:CY7C140/CY7C141)

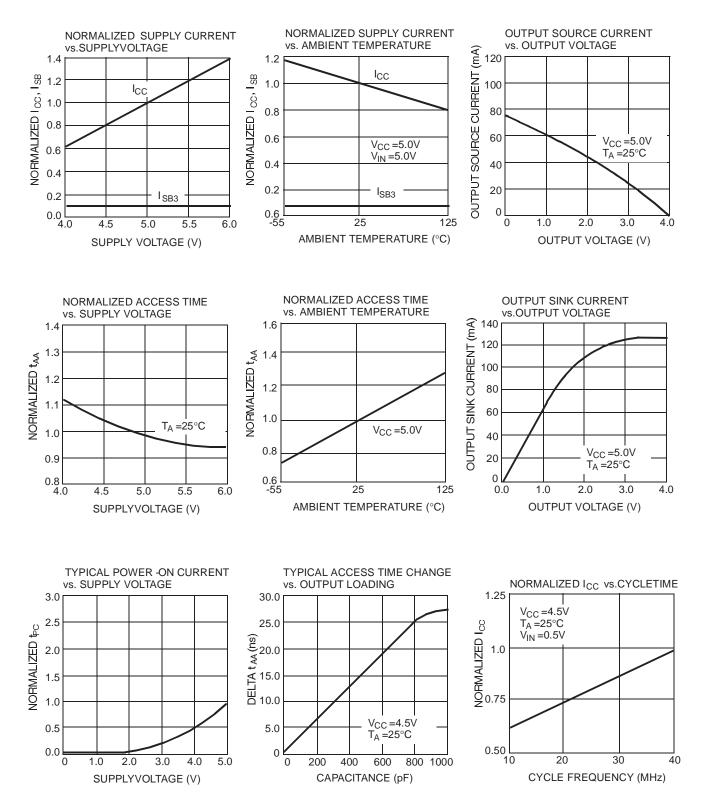








Typical DC and AC Characteristics





Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
30	CY7C130-30PC	P25	48-Lead (600-Mil) Molded DIP	Commercial
	CY7C130-30PI	P25	48-Lead (600-Mil) Molded DIP	Industrial
35	CY7C130-35PC	P25	48-Lead (600-Mil) Molded DIP	Commercial
	CY7C130-35PI	P25	48-Lead (600-Mil) Molded DIP	Industrial
	CY7C130-35DMB	D26	48-Lead (600-Mil) Sidebraze DIP	Military
45	CY7C130-45PC	P25	48-Lead (600-Mil) Molded DIP	Commercial
	CY7C130-45PI	P25	48-Lead (600-Mil) Molded DIP	Industrial
	CY7C130-45DMB	D26	48-Lead (600-Mil) Sidebraze DIP	Military
55	CY7C130-55PC	P25	48-Lead (600-Mil) Molded DIP	Commercial
	CY7C130-55PI	P25	48-Lead (600-Mil) Molded DIP	Industrial
	CY7C130-55DMB	D26	48-Lead (600-Mil) Sidebraze DIP	Military

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
15	CY7C131-15JC	J69	52-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C131-15NC	N52	52-Pin Plastic Quad Flatpack	
25	CY7C131-25JC	J69	52-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C131-25NC	N52	52-Pin Plastic Quad Flatpack	
	CY7C131-25JI	J69	52-Lead Plastic Leaded Chip Carrier	Industrial
	CY7C131-25NI	N52	52-Pin Plastic Quad Flatpack	
30	CY7C131-30JC	J69	52-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C131-30NC	N52	52-Pin Plastic Quad Flatpack	
	CY7C131-30JI	J69	52-Lead Plastic Leaded Chip Carrier	Industrial
35	CY7C131-35JC	J69	52-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C131-35NC	N52	52-Pin Plastic Quad Flatpack	
	CY7C131-35JI	J69	52-Lead Plastic Leaded Chip Carrier	Industrial
	CY7C131-35NI	N52	52-Pin Plastic Quad Flatpack	
45	CY7C131-45JC	J69	52-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C131-45NC	N52	52-Pin Plastic Quad Flatpack	
	CY7C131-45JI	J69	52-Lead Plastic Leaded Chip Carrier	Industrial
	CY7C131-45NI	N52	52-Pin Plastic Quad Flatpack	
55	CY7C131-55JC	J69	52-Lead Plastic Leaded Chip Carrier	Commercial
	CY7C131-55NC	N52	52-Pin Plastic Quad Flatpack]
	CY7C131-55JI	J69	52-Lead Plastic Leaded Chip Carrier	Industrial
	CY7C131-55NI	N52	52-Pin Plastic Quad Flatpack]

Shaded area contains preliminary information.



Ordering Information (continued)

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range		
30	CY7C140-30PC	P25	48-Lead (600-Mil) Molded DIP	Commercial		
	CY7C140-30PI	P25	48-Lead (600-Mil) Molded DIP	Industrial		
35	CY7C140-35PC	P25	48-Lead (600-Mil) Molded DIP	Commercial		
	CY7C140-35PI	P25	48-Lead (600-Mil) Molded DIP	Industrial		
	CY7C140-35DMB	D26	48-Lead (600-Mil) Sidebraze DIP	Military		
45	CY7C140-45PC	P25	48-Lead (600-Mil) Molded DIP	Commercial		
	CY7C140-45PI	P25	48-Lead (600-Mil) Molded DIP	Industrial		
	CY7C140-45DMB	D26	48-Lead (600-Mil) Sidebraze DIP	Military		
55	CY7C140-55PC	P25	48-Lead (600-Mil) Molded DIP	Commercial		
	CY7C140-55PI	P25	48-Lead (600-Mil) Molded DIP	Industrial		
	CY7C140-55DMB	D26	48-Lead (600-Mil) Sidebraze DIP	Military		
Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range		
15	CY7C141-15JC	J69	52-Lead Plastic Leaded Chip Carrier	Commercial		
	CY7C141-15NC	N52	52-Pin Plastic Quad Flatpack	-		
25	CY7C141-25JC	J69	52-Lead Plastic Leaded Chip Carrier	Commercial		
	CY7C141-25NC	N52	52-Pin Plastic Quad Flatpack	1		
	CY7C141-25JI	J69	52-Lead Plastic Leaded Chip Carrier	Industrial		
	CY7C141-25NI	N52	52-Pin Plastic Quad Flatpack	1		
30	CY7C141-30JC	J69	52-Lead Plastic Leaded Chip Carrier	Commercial		
	CY7C141-30NC	N52	52-Pin Plastic Quad Flatpack	-		
	CY7C141-30JI	J69	52-Lead Plastic Leaded Chip Carrier	Industrial		
35	CY7C141-35JC	J69	52-Lead Plastic Leaded Chip Carrier	Commercial		
	CY7C141-35NC	N52	52-Pin Plastic Quad Flatpack	1		
	CY7C141-35JI	J69	52-Lead Plastic Leaded Chip Carrier	Industrial		
	CY7C141-35NI	N52	52-Pin Plastic Quad Flatpack	1		
45	CY7C141-45JC	J69	52-Lead Plastic Leaded Chip Carrier	Commercial		
	CY7C141-45NC	N52	52-Pin Plastic Quad Flatpack	1		
	CY7C141-45JI	J69	52-Lead Plastic Leaded Chip Carrier	Industrial		
	CY7C141-45NI	N52	52-Pin Plastic Quad Flatpack	-		
55	CY7C141-55JC	J69	52-Lead Plastic Leaded Chip Carrier	Commercial		
	CY7C141-55NC	N52	52-Pin Plastic Quad Flatpack	1		
	CY7C141-55JI	J69	52-Lead Plastic Leaded Chip Carrier	Industrial		
	CY7C141-55NI	N52	52-Pin Plastic Quad Flatpack	1		

Shaded area contains preliminary information.



MILITARY SPECIFICATIONS

Group A Subgroup Testing

DC Characteristics

Parameter	Subgroups
V _{OH}	1, 2, 3
V _{OL}	1, 2, 3
V _{IH}	1, 2, 3
V _{IL} Max.	1, 2, 3
I _{IX}	1, 2, 3
I _{OZ}	1, 2, 3
I _{CC}	1, 2, 3
I _{SB1}	1, 2, 3
I _{SB2}	1, 2, 3
I _{SB3}	1, 2, 3
I _{SB4}	1, 2, 3

Switching Characteristics

Parameter	Subgroups
READ CYCLE	
t _{RC}	7, 8, 9, 10, 11
t _{AA}	7, 8, 9, 10, 11
t _{ACE}	7, 8, 9, 10, 11
t _{DOE}	7, 8, 9, 10, 11
WRITE CYCLE	
t _{WC}	7, 8, 9, 10, 11
t _{SCE}	7, 8, 9, 10, 11
t _{AW}	7, 8, 9, 10, 11
t _{HA}	7, 8, 9, 10, 11
t _{SA}	7, 8, 9, 10, 11
t _{PWE}	7, 8, 9, 10, 11
t _{SD}	7, 8, 9, 10, 11
t _{HD}	7, 8, 9, 10, 11

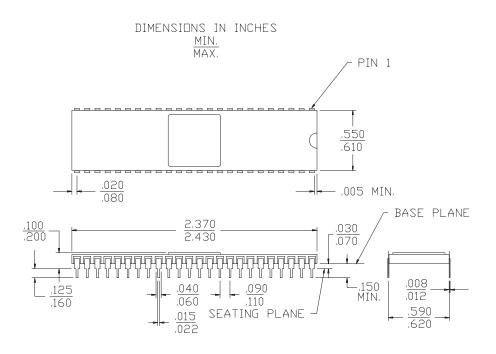
Parameter	Subgroups
BUSY/INTERRUPT TIMING	
t _{BLA}	7, 8, 9, 10, 11
t _{BHA}	7, 8, 9, 10, 11
t _{BLC}	7, 8, 9, 10, 11
t _{BHC}	7, 8, 9, 10, 11
t _{PS}	7, 8, 9, 10, 11
t _{WINS}	7, 8, 9, 10, 11
t _{EINS}	7, 8, 9, 10, 11
t _{INS}	7, 8, 9, 10, 11
t _{OINR}	7, 8, 9, 10, 11
t _{EINR}	7, 8, 9, 10, 11
t _{INR}	7, 8, 9, 10, 11
BUSY TIMING	
t _{WB} [24]	7, 8, 9, 10, 11
t _{WH}	7, 8, 9, 10, 11
t _{BDD}	7, 8, 9, 10, 11

Note:

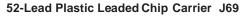
24. CY7C140/CY7C141 only. Document #: 38-00027-L

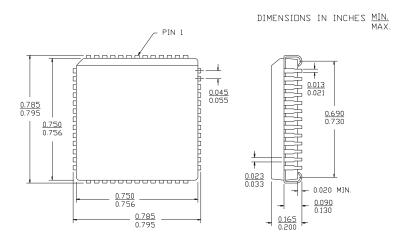


Package Diagrams



48-Lead (600-Mil) Sidebraze DIP D26

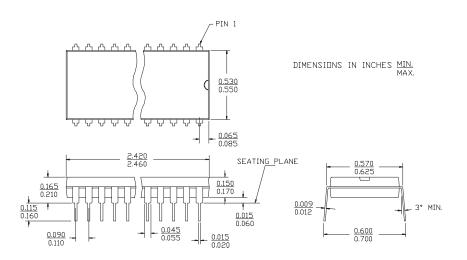






Package Diagrams (continued)

48-Lead (600-Mil) Molded DIP P25



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